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U.S. PATENT DOCUMENTS									
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate			
TH	AA 6 2 7 0 5 6 9	08/2001	Shibata et al.						
TH	AB 6 1 7 7 0 5 7	01/2001	Purdy						
TH	AC 5 8 6 8 8 3 7	02/1999	DiSalvo et al.						
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	AE								
	AF								
	AG								

FOREIGN PATENT DOCUMENTS									
Document Number	Date	Country	Class	Subclass	Translation				
					Yes	No			
AH									
AI									

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	
TH	AJ "Preparation of GaN Single Crystals Using a Na Flux", H. Yamane et al., Chemical Mater, 1997, Vol. 9, No. 2, pp. 413-416.
TH	AK "InGaN/GaN/AlGaIn-Based Laser Diodes With Cleaved Facets Grown on GaN Substrates", S. Nakamura et al., Applied Physics Letters, 1998, Vol. 73, No. 6, pp. 832-834.
TH	AL "Bulk and Homoepitaxial GaN-growth and Characterization", S. Porowski, Journal of Crystal Growth, 1998, Vol. 189/190, pp.153-158.
TH	AM "InGaN/GaN/AlGaIn-Based Laser Diodes With Modulation-Doped Strained-Layer Superlattices", S. Nakamura et al., Japanese Journal of Applied Physics, 1997, Vol. 36, No. 12A, pp. 1568-1571.
	AN

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609: Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.